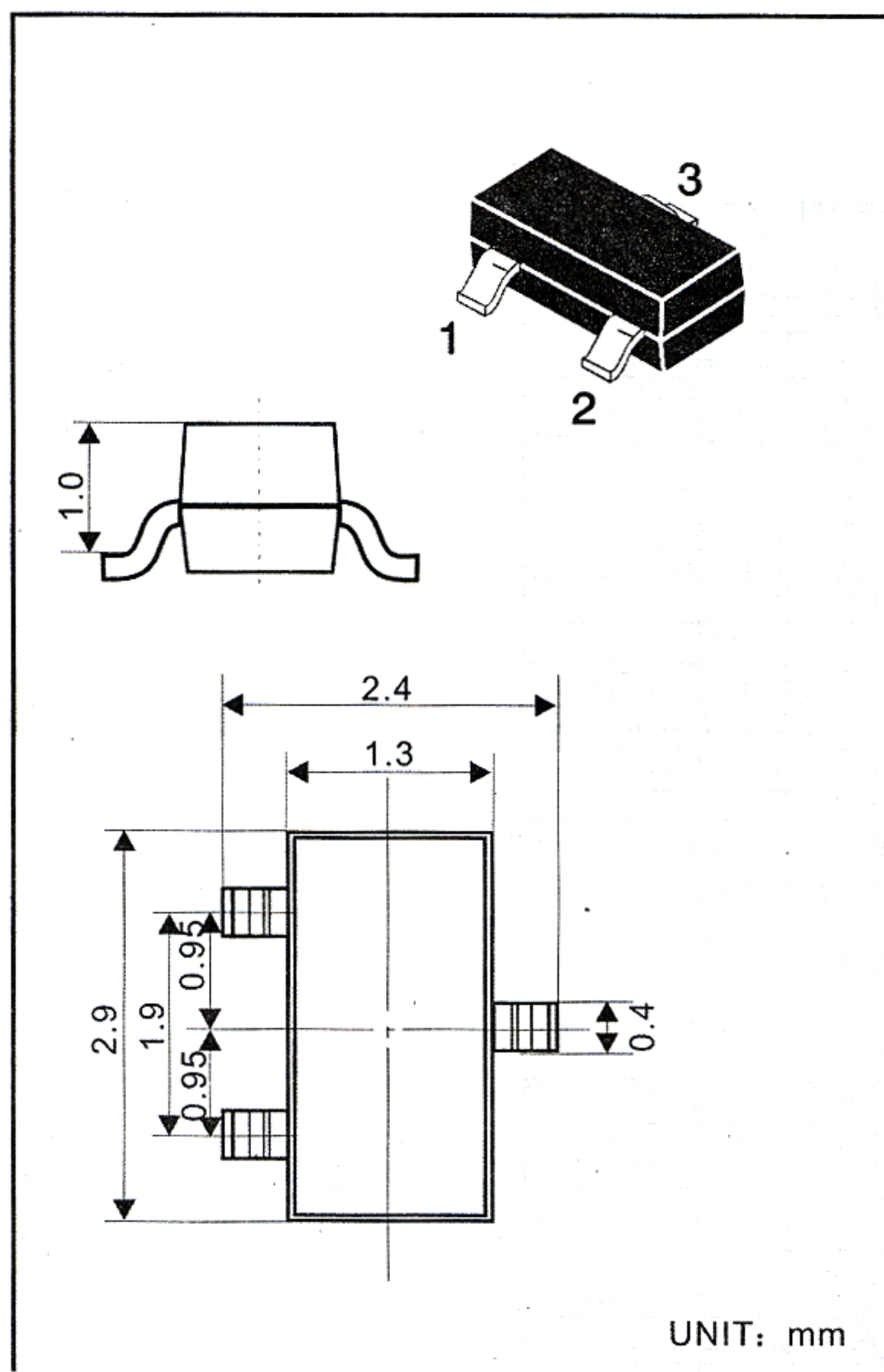


BAL99LT1 SWITCHING DIODE



FEATURES

Power dissipation

P_D : 225mW ($T_{amb}=25^\circ C$)

Forward current

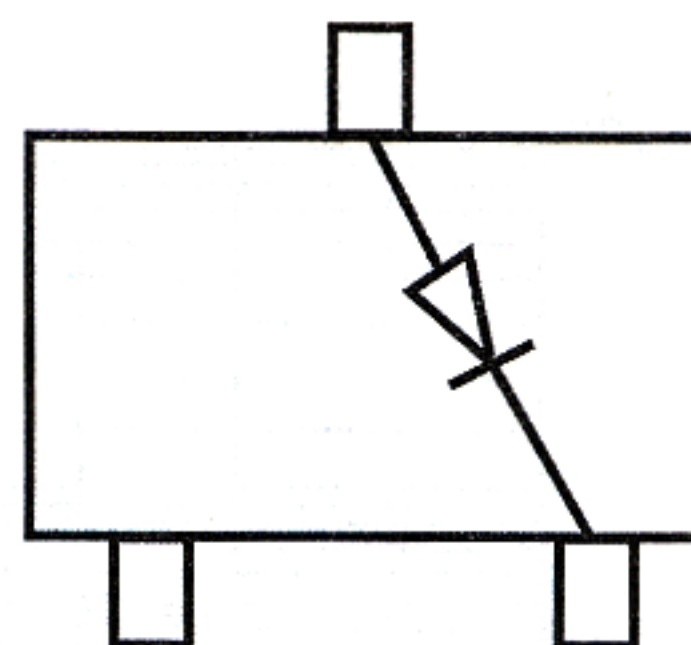
I_F : 100mA

Reverse voltage

V_R : 70V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^\circ C$ to $+150^\circ C$

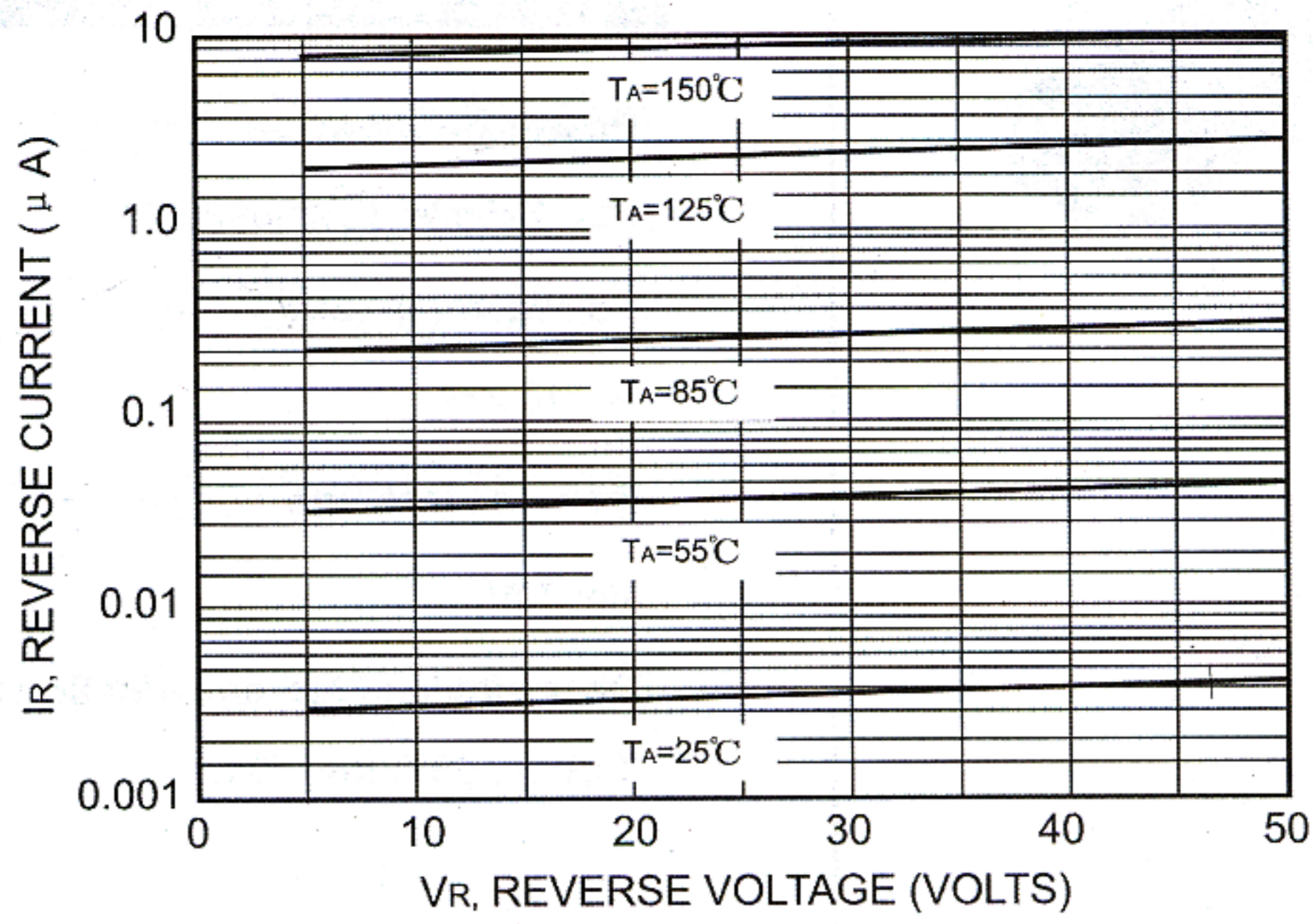


MARKING: JF

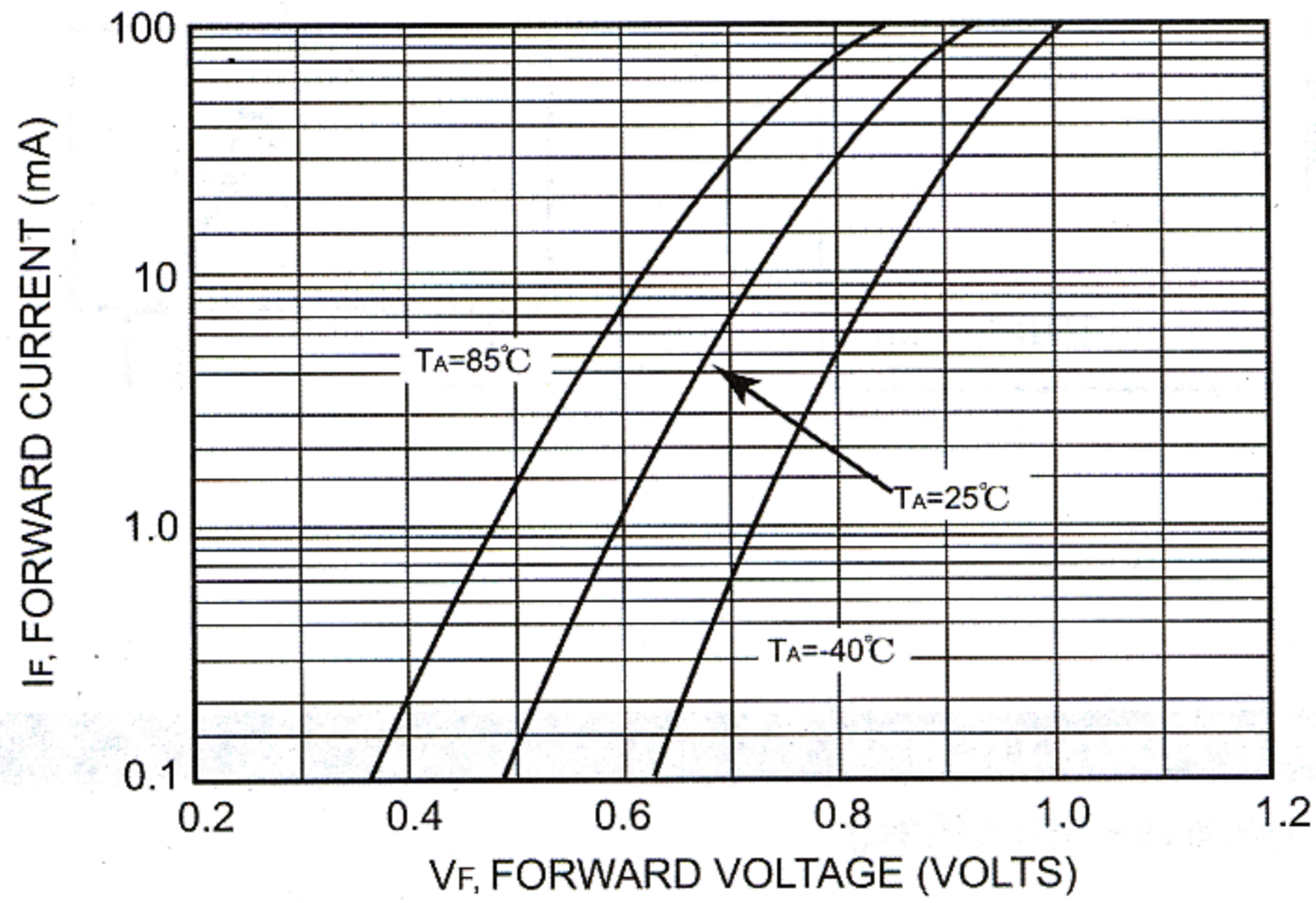
ELECTRICAL CHARACTERISTICS

($T_{amp}=25^\circ C$ unless otherwise specified)

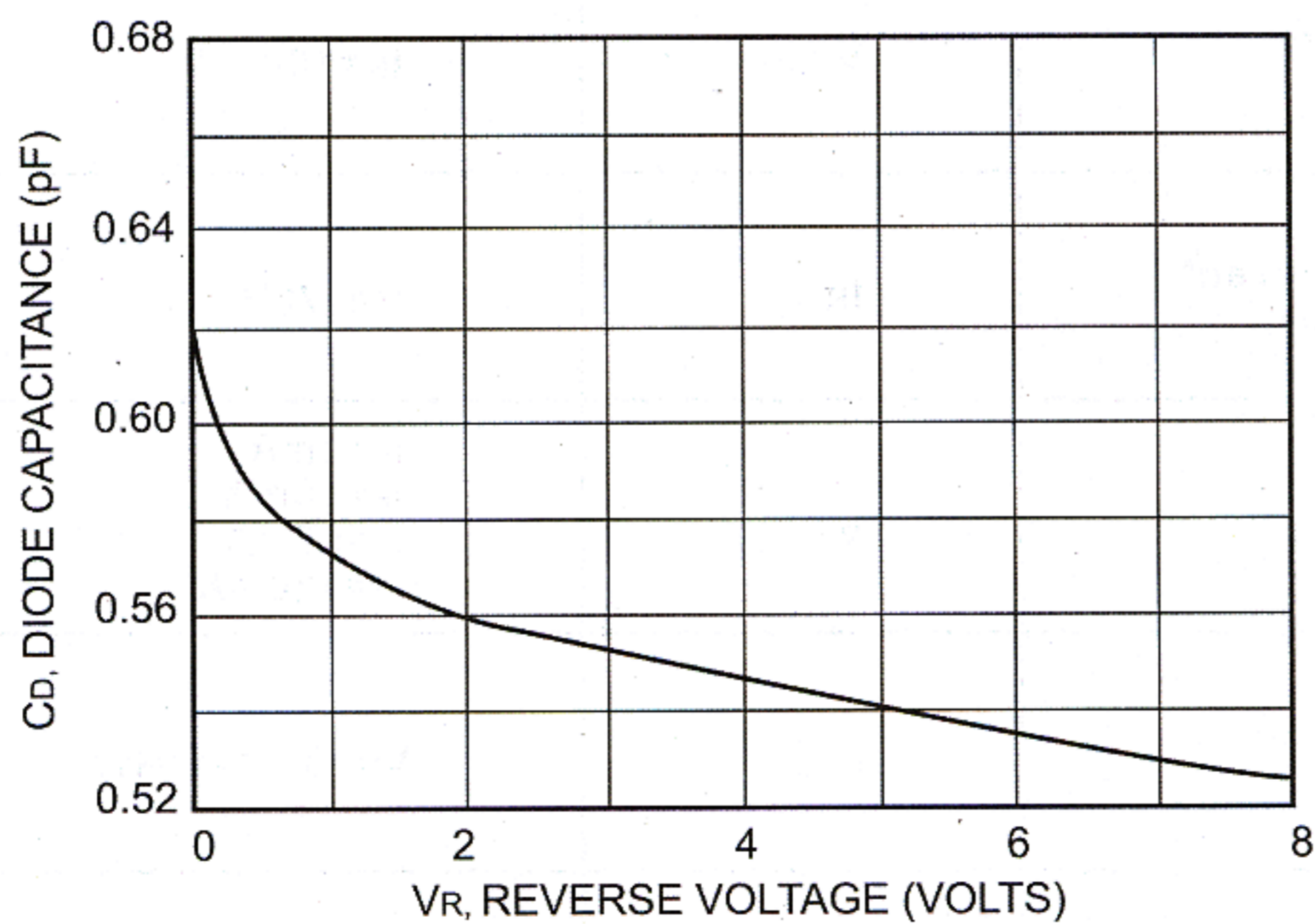
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	70		V
Reverse voltage leakage current	I_R	$V_R=70V$		2.5	μA
Forward voltage	V_F	$I_F=1mA$ $I_F=10mA$ $I_F=50mA$ $I_F=150mA$		715 855 1000 1250	mV
Diode capacitance	C_{tot}	$V_R=0V, f=1MHz$		1.5	pF
Reverse recovery time	t_{rr}	$I_F=I_R=10mA$ $I_{rr}=0.1I_R$		6	ns



Leakage Current



Forward Voltage



Capacitance